

# BUK9616-75B

# N-channel TrenchMOS logic level FET

Rev. 02 — 16 February 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	75	V
$I_D$	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	67	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	157	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	12	14	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{Figure 12}};$ see Figure 12	-	14	16.4	mΩ



### N-channel TrenchMOS logic level FET

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 67 \text{ A}; V_{sup} \le 75 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; unclamped$	-	-	140	mJ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 60 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 13	-	14	-	nC

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate		_	
2	D	drain[1]	mb	D	
3	S	source			
mb	D	mounting base; connected to drain	1 3	mbb076 S	
			SOT404 (D2PAK)		

<sup>[1]</sup> It is not possible to make a connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9616-75B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	75	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
$V_{GS}$	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	67	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; see <u>Figure 1</u>	-	47	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3	-	270	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	157	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	67	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	270	Α
Avalanche r	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 67 \text{ A}; V_{\text{sup}} \le 75 \text{ V}; R_{\text{GS}} = 50 \Omega;$ $V_{\text{GS}} = 5 \text{ V}; T_{\text{j(init)}} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	140	mJ

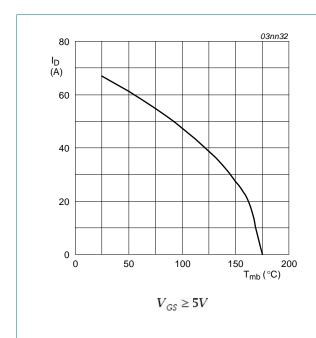


Fig 1. Normalized continuous drain current as a function of mounting base temperature

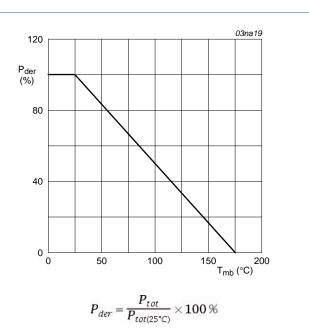
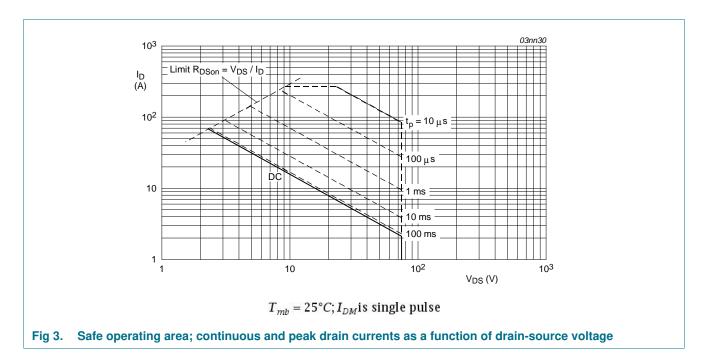


Fig 2. Normalized total power dissipation as a function of mounting base temperature



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

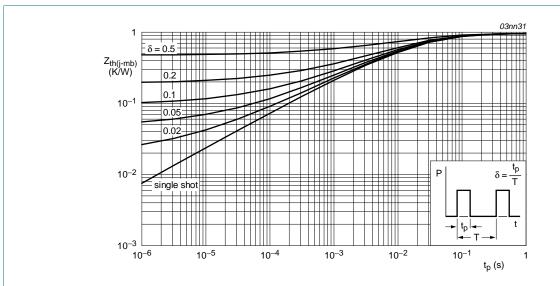


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

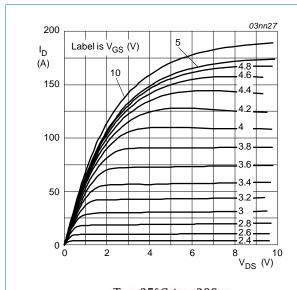
# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	75	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	70	-	-	V
()	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see <u>Figure 10</u>	-	-	2.3	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u>	1.1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see <u>Figure 10</u>	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	12	14	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	18	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	34	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	14	16.4	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 5 \text{ V};$	-	35	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	6	-	nC
$Q_{GD}$	gate-drain charge		-	14	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	3026	4034	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	301	361	рF
$C_{rss}$	reverse transfer capacitance		-	140	191	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	30	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$ ; $T_j = 25 °C$	-	102	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	101	-	ns
t <sub>f</sub>	fall time		-	57	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
		from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead 6 mm from package to source bond pad; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	96	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	138	-	nC



 $T_j=25^{\circ}C; t_p=300\mu s$ 

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

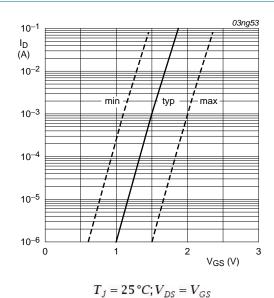
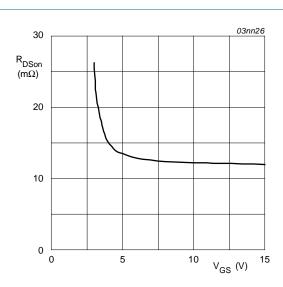
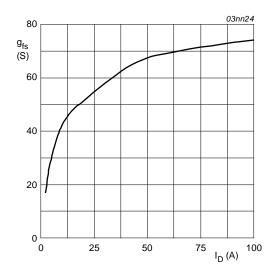


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j=25^{\circ}C; V_{DS}=25V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

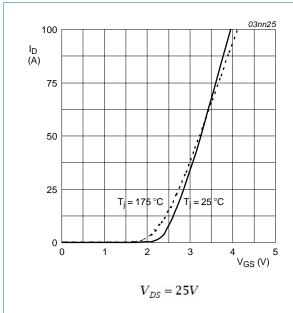


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

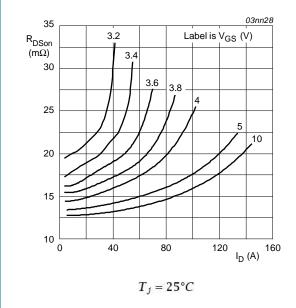


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

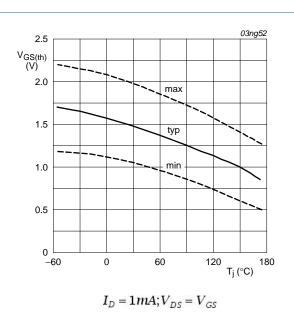


Fig 10. Gate-source threshold voltage as a function of junction temperature

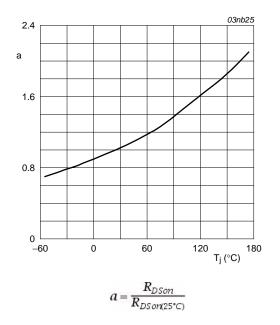


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

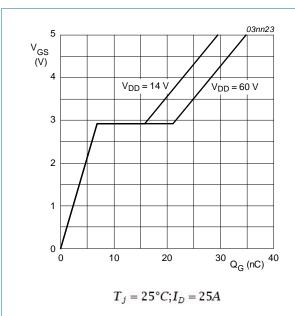
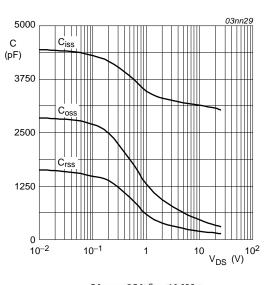


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

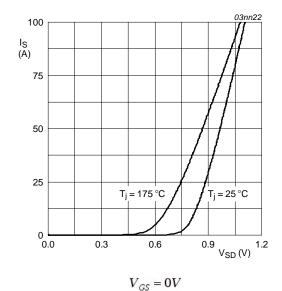


Fig 15. Source current as a function of source-drain voltage; typical values

## 7. Package outline

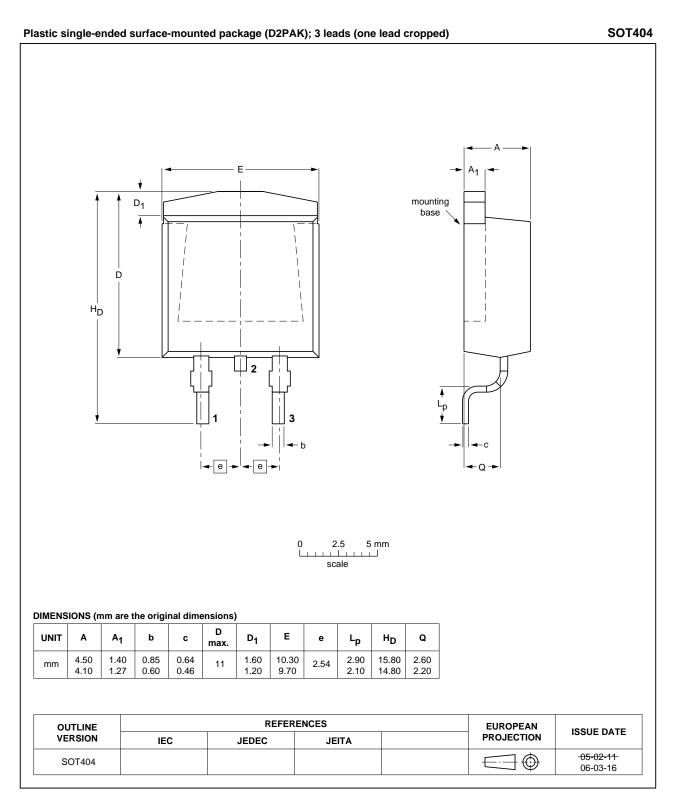


Fig 16. Package outline SOT404 (D2PAK)

N-channel TrenchMOS logic level FET

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9616-75B v.2	20110216	Product data sheet	-	BUK95_9616_75B v.1
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guid of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>			, ,
	<ul> <li>Type number BUK</li> </ul>	9616-75B separated from	data sheet BUK95_9616	6_75B v.1.
BUK95_9616_75B v.1 (9397 750 11246)	20030423	Product data	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# BUK9616-75B

## **Nexperia**

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